



Application No. 09/640,519  
Docket No. 740819-408

*Image*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:	)	
NAKAOKA, Hiroaki	)	Examiner: David Vu
Serial No. 09/640,519	)	Group Art Unit: 2818
Filed: August 17, 2000	)	
For: METHOD OF FABRICATING	)	Confirmation No. 6287
SEMICONDUCTOR DEVICE	)	

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

The Commissioner is hereby authorized to charge \$180 to deposit account no. 19-2380 to comply with the provisions of 37 C.F.R. § 1.97(c)

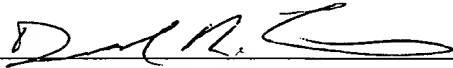
The undersigned certifies that either (1) each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in connection with a counterpart foreign application not more than three (3) months prior to the filing of this statement, or (2) no item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application and to my knowledge after making reasonable inquiry, was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing of this statement.

Enclosed is a copy of the Notice of Reasons of Rejection dated December 24, 2003, for a corresponding Japanese patent application together with the references cited therein.

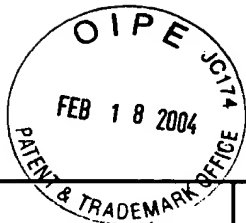
It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380. (740819-408)

Respectfully submitted,  
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Substitute for form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	09/640,519
				Filing Date	August 17, 2000
				First Named Inventor	Hiroaki NAKAOKA
				Art Unit	2818
				Examiner Name	David Vu
Sheet	1	of	1	Attorney Docket Number	740819-408

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		LAI, ET AL., "A COMPARISON BETWEEN NO-ANNEALED 0 <sub>2</sub> -AND N <sub>2</sub> O-GROWN GATE DIELECTRICS", PROCEEDINGS 1998 IEEE HONG KONG ELECTRON DEVICES MEETING, PP. 36-39, AUGUST 29, 1998, CHINA	
		LIN, ET AL., "LEAKAGE CURRENT, RELIABILITY CHARACTERISTICS, AND BORON PENETRATION OF ULTRA-THIN (32-36Å) O <sub>2</sub> -OXIDES AND N <sub>2</sub> O/NO OXYNITRIDES", IEDM 96, PP. 331-334, 1996	
		SUN, ET AL., "MOS CHARACTERISTICS OF N <sub>2</sub> O-GROWN AND NO-ANNEALED OXYNITRIDES", 4 <sup>TH</sup> INTERNATIONAL TECHNOLOGY PROCEEDINGS, PP. 90-92, NOVEMBER 1995	
		NOTICE OF REASONS OF REJECTION DATED DECEMBER 24, 2003	

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.